

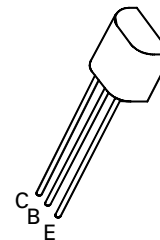
NPN SILICON PLANAR MEDIUM POWER TRANSISTORS

ISSUE 2 – MARCH 1994

ZTX452 ZTX453

FEATURES

- * 100 Volt V_{CEO}
- * 1 Amp continuous current
- * $P_{tot} = 1$ Watt



E-Line
T092 Compatible

ABSOLUTE MAXIMUM RATINGS.

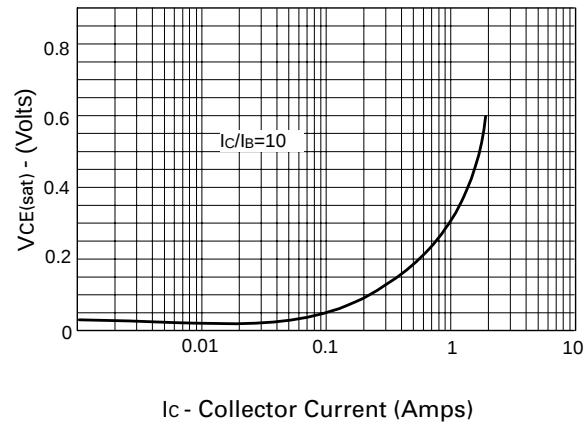
PARAMETER	SYMBOL	ZTX452	ZTX453	UNIT
Collector-Base Voltage	V_{CBO}	100	120	V
Collector-Emitter Voltage	V_{CEO}	80	100	V
Emitter-Base Voltage	V_{EBO}	5		V
Peak Pulse Current	I_{CM}	2		A
Continuous Collector Current	I_C	1		A
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	1		W
Operating and Storage Temperature Range	$T_j: T_{stg}$	-55 to +200		$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

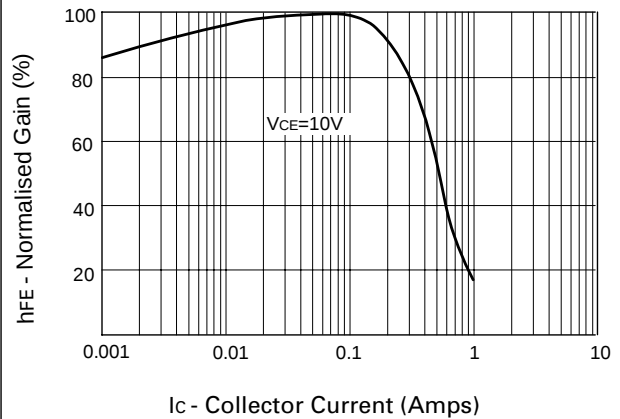
PARAMETER	SYMBOL	ZTX452		ZTX453		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	100		120		V	$I_C=100\mu A$
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	80		100		V	$I_C=10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5		5		V	$I_E=100\mu A$
Collector Cut-Off Current	I_{CBO}		0.1		0.1	μA	$V_{CB}=80V$ $V_{CB}=100V$
Emitter Cut-Off Current	I_{EBO}		0.1		0.1	μA	$V_{EB}=4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.7		0.7	V	$I_C=150mA$, $I_B=15mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.3		1.3	V	$I_C=150mA$, $I_B=15mA^*$
Static Forward Current Transfer Ratio	h_{FE}	40 10	150	40 10	200		$I_C=150mA$, $V_{CE}=10V^*$ $I_C=1A$, $V_{CE}=10V^*$
Transition Frequency	f_T	150		150		MHz	$I_C=50mA$, $V_{CE}=10V$ $f=100MHz$
Output Capacitance	C_{obo}		15		15	pF	$V_{CB}=10V$, $f=1MHz$

ZTX452 ZTX453

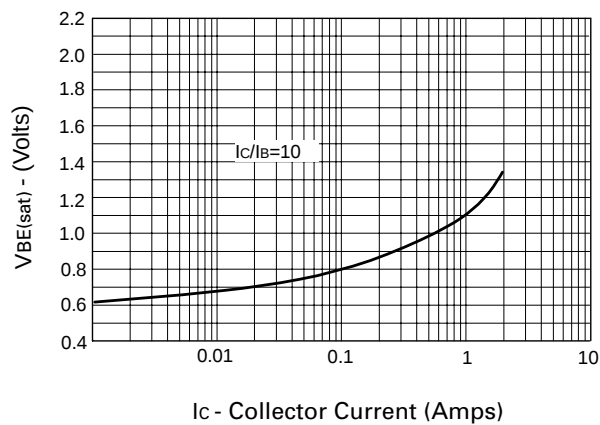
TYPICAL CHARACTERISTICS



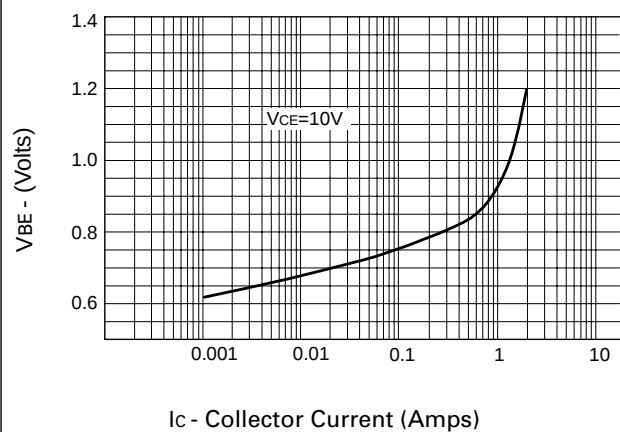
$V_{CE(sat)}$ v I_C



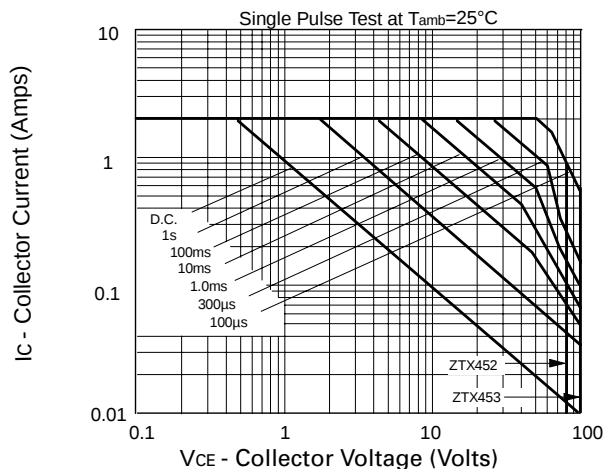
h_{FE} v I_C



$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C



Safe Operating Area